IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: **Xiang, et al.**

Serial No.: **10/643,461**

Filed: **August 18, 2003**

For: **Field Effect Transistor Having Increased Carrier Mobility**

Art Unit: **2815**

Examiner: **Nguyen, Joseph H.**

INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir/Madam:

In this Information Disclosure Statement and pursuant to 37 C.F.R. §§ 1.56 and 1.97, Applicants hereby disclose to the Patent Office patents, publications or other information of which Applicants are aware. A copy of a Form 1449 identifying the patents and other materials is submitted herewith.

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The Assistant Commissioner is hereby authorized to charge or credit Deposit Account Number 50-0731 for any deficiency or overpayment in the fees required for the filing of this Information Disclosure Statement, for which purpose a duplicate copy of this paper is also included.

Respectfully submitted,
Farjami & Farjami LLP

Dated: 3/9/05

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FORM PTO-1449	ATTY. DOCKET NO. 0180144	SERIAL NO. 10/643,461
LIST OF PATENTS AND OTHER ITEMS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	APPLICANTS: Xiang, et al.	
	FILING DATE: August 18, 2003	GROUP ART: 2815

U.S. PATENT DOCUMENTS

Exam. Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	1	6,262,462	7/17/2001	Marshall, et al.			
	2	5,721,145	2/24/1998	Kusakabe, et al.			
	3	2002/093046 A1	7/18/2002	Moriya, et al.			

FOREIGN PATENT DOCUMENTS

Exam. Initials		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANSLATION YES	TRANSLATION NO
	1	WO 2004/112147 A1	12/23/2004	WIPO				
	2	EP 1 164 636 A2	12/19/2001	EPO				
	3	JP 05082777	4/2/1993	JPO				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

	1	Ota et al, *Novel Locally Strained Channel Technique for High Performance 55nm CMOS*, IEDM Technical Digest, 27-30 (2002)
	2	*Applying Mechanical Stress to Improve MOS Semiconductor Performance*, 30 IBM Technical Disclosure Bulletin, 330-333 (1988)
	3	Momose et al, *Relationship Between Mobility and Residual-Mechanical-Stress As Measured By Raman Spectroscopy For Nitrided-Oxide-Gate MOSFETs*, 90 IEDM, 65-68 (1990)
	4	Jennifer O'Connor, *Analytical Predictions of Thermal Stress in MOSFETs*, IEEE, 131-143 (1995)
	5	Wristers et al, *Ultra Thin Oxide Reliability: Effects of Gate Doping Concentration and Poly-Si/SiO2 Interface Stress Relaxation*, IEEE, 77-83 (1996)
	6	Steegen et al, *Silicide-induced Stress In Si: Origin and Consequences for MOS Technologies*, 38 Materials Science and Engineering R: Reports, 1-53 (2002)

EXAMINER:	DATE CONSIDERED:

EXAMINER: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.
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